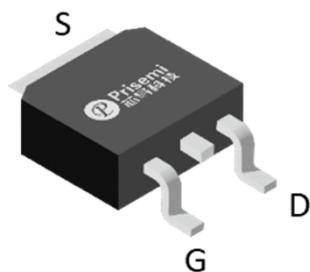


Description

Product Summary		
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ)	I _D (A)
700	480	5

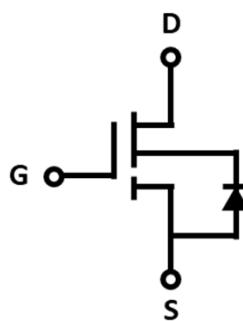


Feature

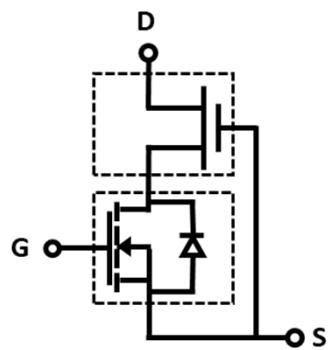
- Easy to use, compatible with standard gate drivers
- Excellent Q_G × R_{DS(on)} figure of merit (FOM)
- Low Q_{RR}, no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors



Schematic Symbol



Cascode
Device Structure

Absolute maximum rating@25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	700	V
Gate-Source Voltage	V _{GS}	±20	V
Transient Drain-Source Voltage ¹⁾	V _{TDS}	800	V
Continuous Drain Current	I _D	5	A
		3.2	
Pulsed Drain Current (Pulse Width: 100μs)	I _{DM}	12.3	A
		9.4	
Power Dissipation	P _D	22	W
Soldering Peak Temperature	T _{CSOLD}	260	°C
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to 150	°C

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	-	5.5	-	°C/W
Thermal Resistance, Junction-to-Ambient ²⁾	R _{θJA}	-	50	-	°C/W

700V GaN Power Transistor

PGCDP70R480B

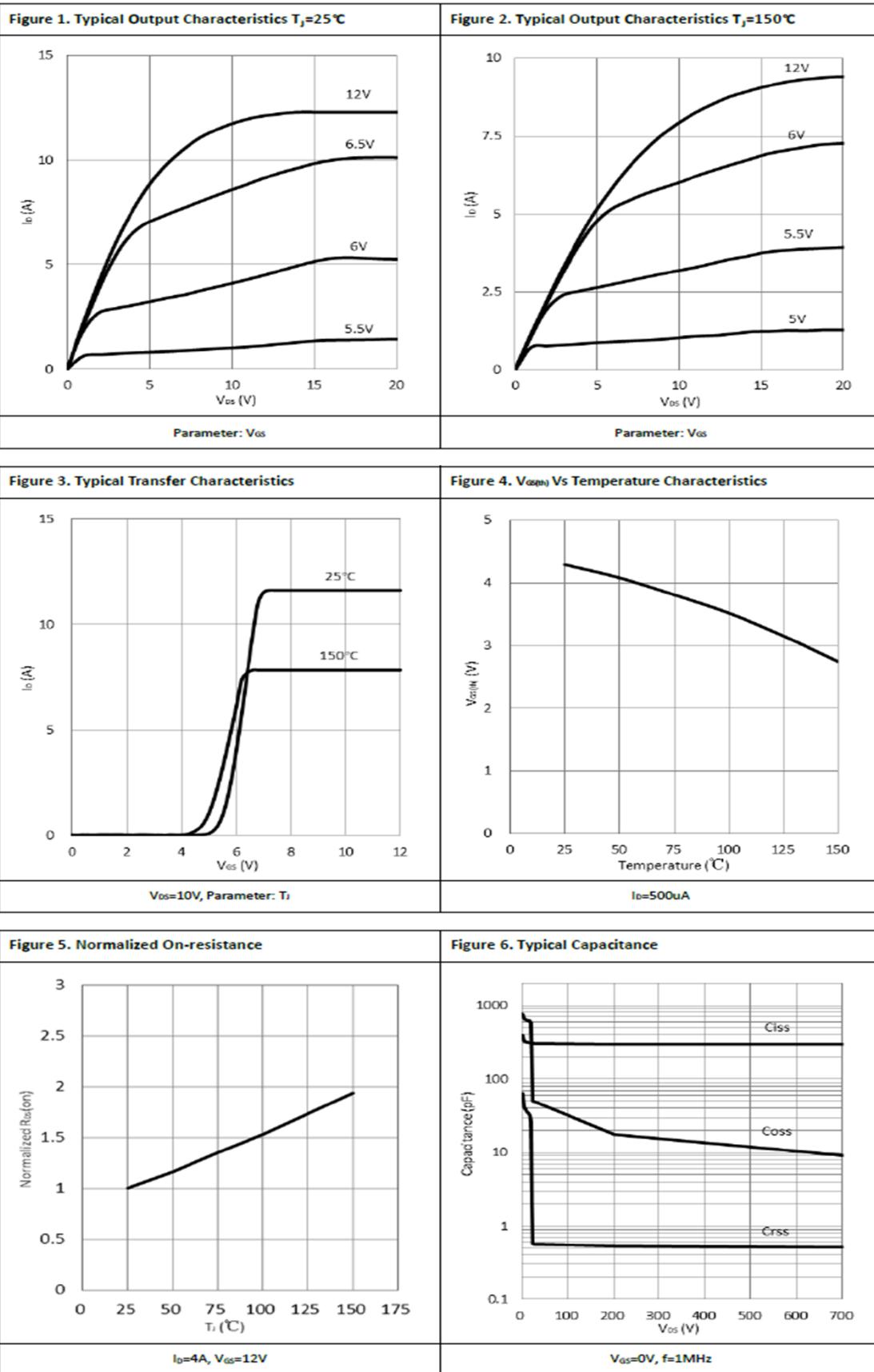
Electrical characteristics per line@25°C (unless otherwise specified)

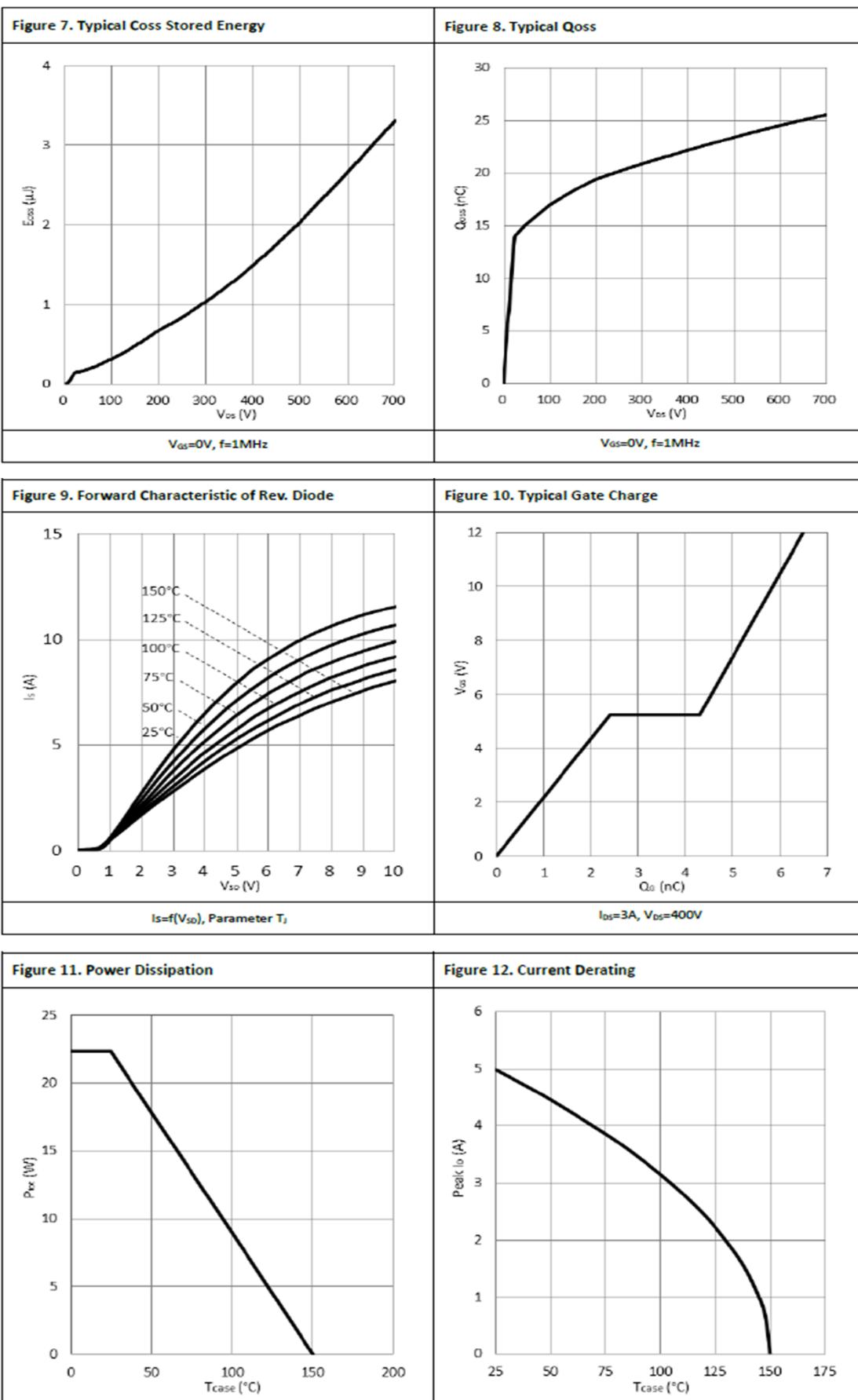
Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units	
Statistic Characteristics								
Maximum Drain-Source Voltage	V _{DS-Max}	V _{GS} = 0V		700	-	-	V	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA		-	1000	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =700V, V _{GS} =0V	T _J =25°C	-	8	20	μA	
			T _J =150°C	-	50	-		
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V		-	-	±150	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 500μA	3	4	5	-	V	
Gate threshold voltage temperature coefficient	△V _{GS(th)} /T _J			-	-13	-	mV/°C	
Drain-Source On-State Resistance ³⁾	R _{DS(ON)}	V _{GS} =12V, I _D =2A	T _J =25°C	-	480	600	mΩ	
			T _J =150°C	-	960	-		
Dynamic Characteristics								
Input Capacitance	C _{iss}	V _{DS} = 400V, V _{GS} = 0V, f = 1MHz	- - -	298	-	-	pF	
Output Capacitance	C _{oss}			12.6	-	-		
Reverse Transfer Capacitance	C _{rss}			0.5	-	-		
Effective Output Capacitance, Energy Related	C _{o(er)}	V _{GS} = 0V, V _{DS} = 0-400V	- - -	18.6	-	-	pF	
Effective Output Capacitance, Time Related	C _{o(tr)}			51.6	-	-		
Output Charge	Q _{oss}			21	-	nC		
Turn-on Delay Time	t _{d(on)}	V _{DS} = 400V, I _D = 3.6A, V _{GS} = 0-12V, R _G = 47Ω	- - - -	44	-	-	ns	
Turn-on Rise Time	t _r			10	-	-		
Turn-Off Delay Time	t _{d(off)}			44	-	-		
Turn-Off Fall Time	t _f			8	-	-		
Total Gate Charge	Q _g	V _{DS} = 400V, I _D = 3A, V _{GS} = 0-12V	- - -	6.5	-	-	nC	
Gate-Source Charge	Q _{gs}			2.4	-	-		
Gate-Drain Charge	Q _{gd}			1.9	-	-		
Reverse Diode Characteristics								
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1.6A		-	1.5	-	V	
		V _{GS} =0V, I _S =3A	T _J =25°C	-	2	-		
			T _J =150°C	-	3.2	-		
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =3A, V _{DD} =400V, di/dt=1000A/μs		-	15	-	ns	
Reverse Recovery Charge	Q _{rr}			-	21	-	μC	

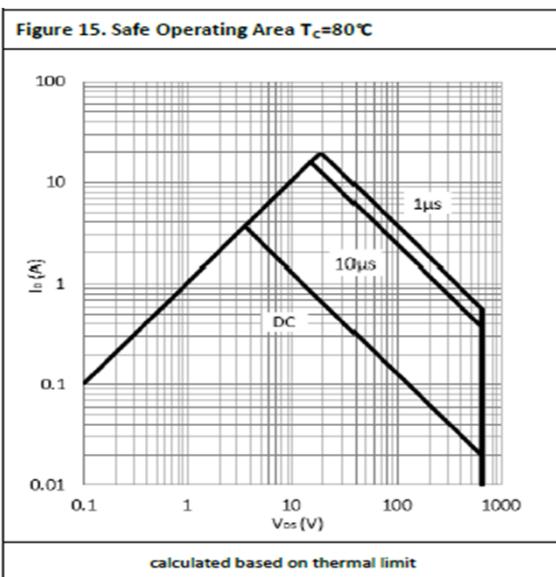
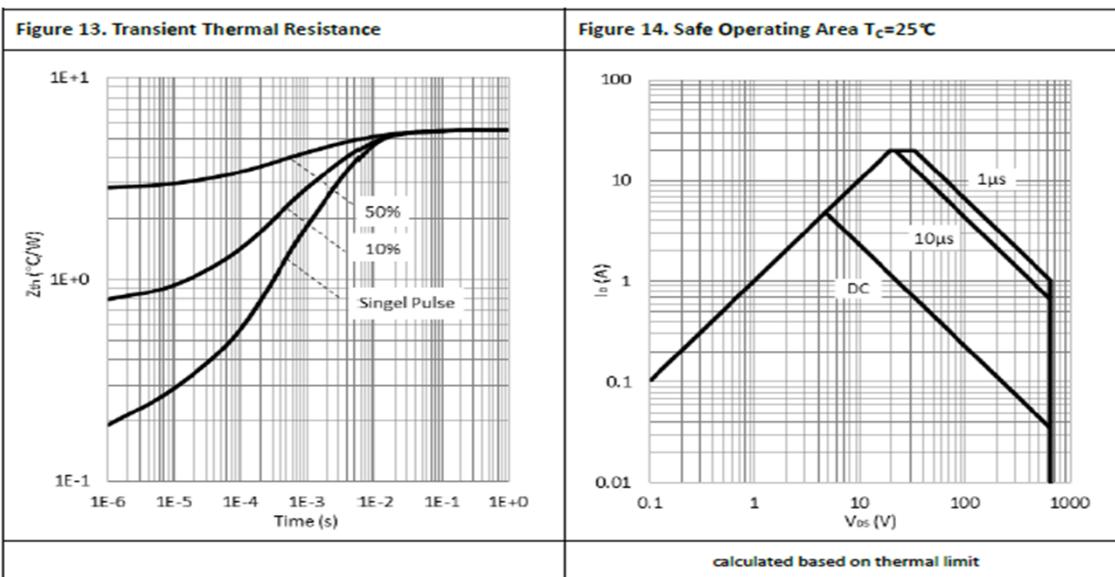
Notes:

1. Off-state spike duty cycle < 0.01, spike duration < 2μs
2. Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70μm thickness)
3. Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

Typical Characteristics







Test Circuits and Waveforms

Figure 16. Switching Time Test Circuit

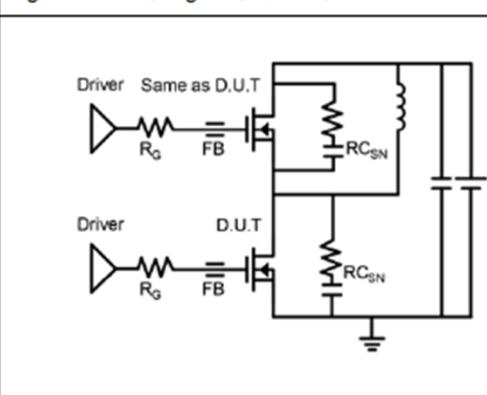


Figure 17. Switching Time Waveform

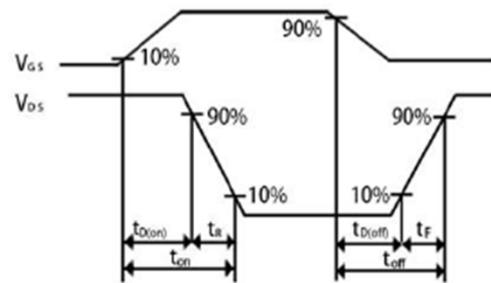


Figure 18. Dynamic R_DS(on) Test Circuit

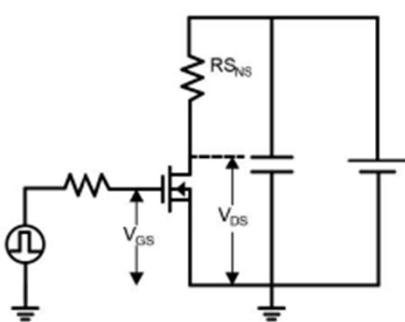


Figure 19. Dynamic R_DS(on) Waveform

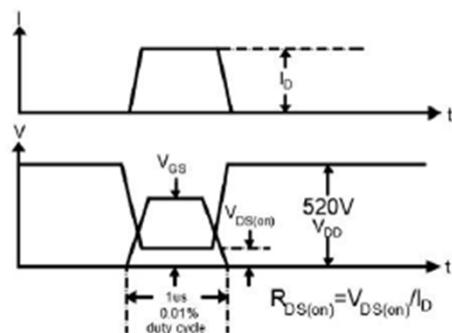


Figure 20. Diode Characteristic Test Circuits

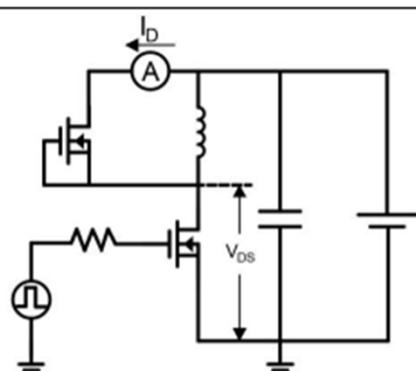
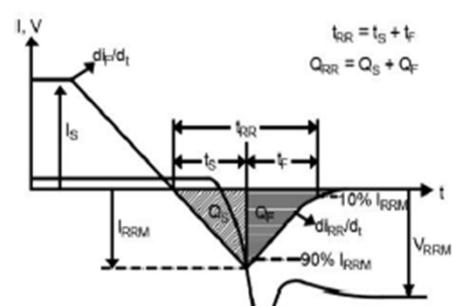
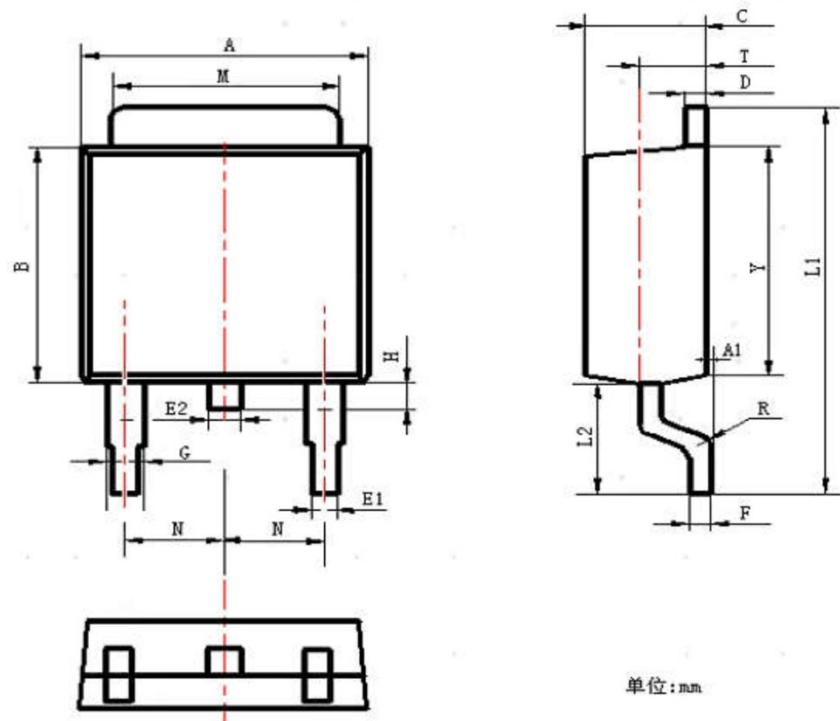


Figure 21. Diode Recovery Waveform



Product Dimension (TO-252)



SYMBOL	Millimeter		
	Min	Nom	Max
A	6.30	6.60	6.90
A1	0	0.80	0.16
B	5.70	6.00	6.30
C	2.10	2.30	2.50
D	0.30	0.60	0.90
E1	0.60	0.75	0.90
F	0.30	0.45	0.60
G	0.70	0.95	1.20
L1	9.30	9.90	10.50
L2	2.50	2.80	3.10
H	0.40	0.70	1.05
M	4.90	5.30	5.60
N	2.09	2.29	2.49

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